

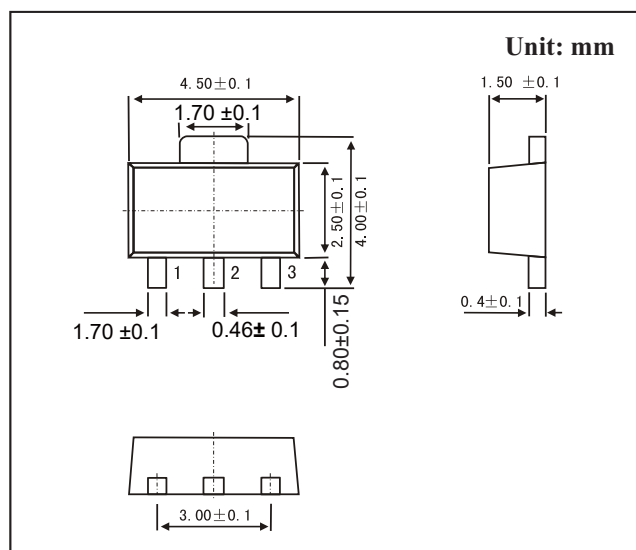
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Large collector power dissipation PC
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

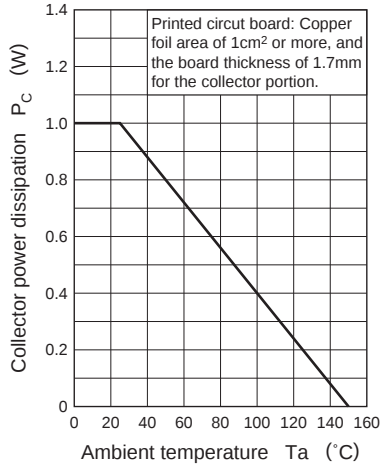
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-30	V
Collector - Emitter Voltage	V _{CEO}	-25	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-1	A
Collector Current - Pulse	I _{CP}	-1.5	
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

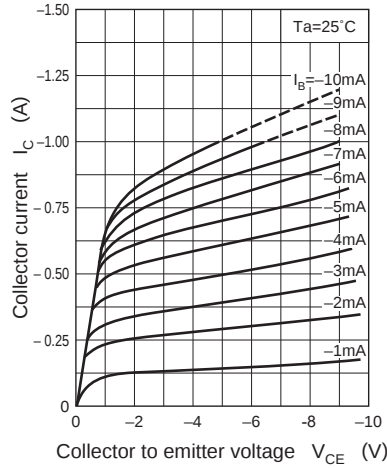
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E =0	-30			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -2 mA, I _B =0	-25			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -20 V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50mA		-0.2	-0.4	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B =-50mA		-0.85	-1.2	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C = -500mA	85		340	
	h _{FE(2)}	V _{CE} = -5V, I _C = -1A	50			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		20	30	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA, f=200MHz		200		MHz

RATINGS AND CHARACTERISTIC CURVES

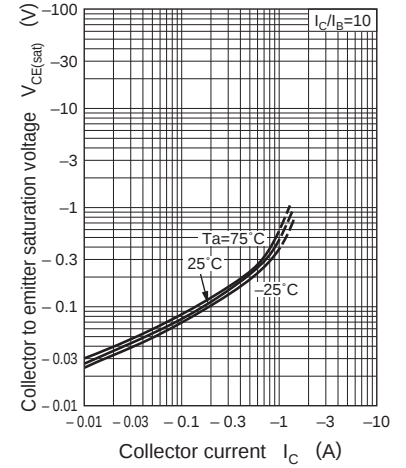
$P_C - T_a$



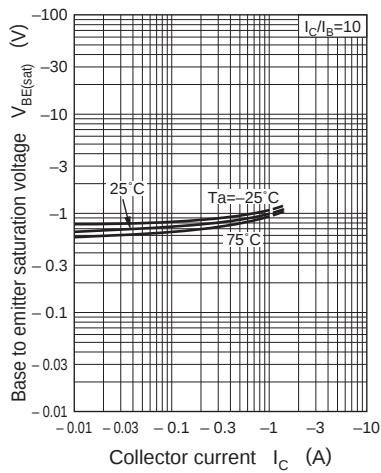
$I_C - V_{CE}$



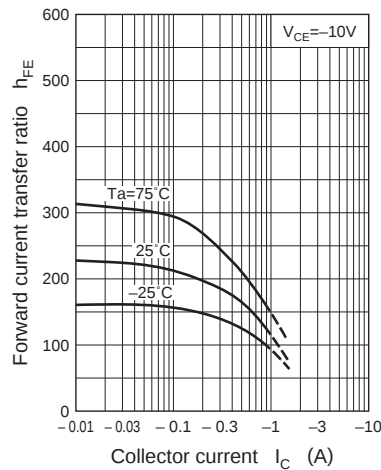
$V_{CE(sat)} - I_C$



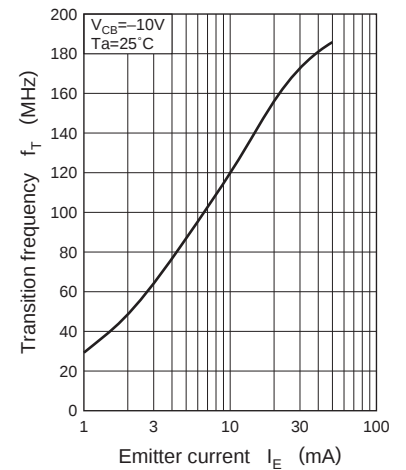
$V_{BE(sat)} - I_C$



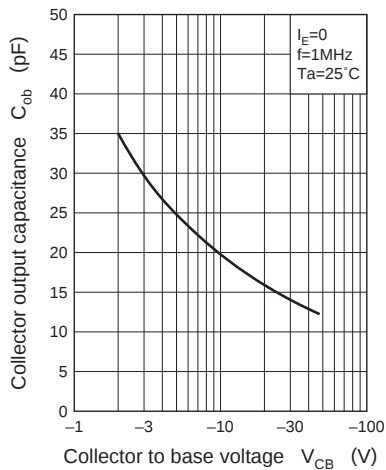
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



Area of safe operation (ASO)

